

**II B.Tech II Semester Examinations, April/May 2012**  
**SEMI CONDUCTOR DEVICES AND CIRCUITS**

**Mechatronics**

**Time: 3 hours**

**Max Marks: 80**

**Answer any FIVE Questions**  
**All Questions carry equal marks**

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1. (a) Prove that the concentration of holes in an intrinsic semiconductor is given by  

$$P = N_{VX} e^{-(E_F - E_V)/kT}$$
 (b) Define Mass Action Law & Law of junction in semiconductors. [10+6]
2. (a) Draw the circuit diagram of Clapp oscillator and explain the operation. Enumerate advantages of this over the Colpitt's or Hartely oscillator.  
 (b) In Colpitt's oscillator circuit,  $C_1 = 1\text{nF}$ ,  $C_2 = 10\text{nF}$ ,  $L = 110\mu\text{H}$ . Find feedback factor and operating frequency. [10+6]
3. Derive all the necessary parameters of HWR and explain. [16]
4. (a) When an electron is placed in a magnetic field with a period of rotation  $T = [35.5/B] 10^{-12}$  sec. Show that the trajectory of electron is a circle.  
 (b) What is the radius described by an electron placed in a magnetic field, perpendicular to its motion, when the accelerating potential is 900V, and  $B = 0.01\text{wb/m}^2$ . What is the time period of rotation? [8+8]
5. (a) Explain the operation of n - channel JFET with a neat sketch and draw the characteristics.  
 (b) For a fixed bias circuit shown figure 4.  $I_{DSS} = 6\text{mA}$ ,  $V_P = -6\text{V}$ . Find drain current and  $V_{DS}$ . [8+8]

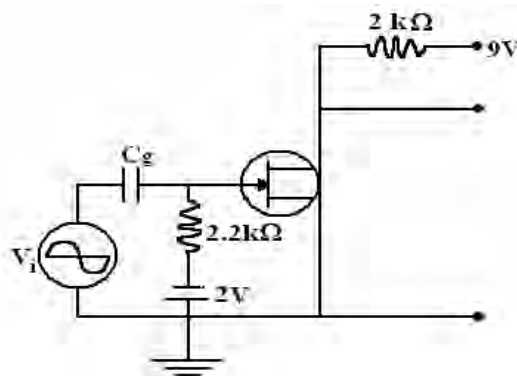


Figure 1:

6. (a) What are the different configurations of BJT? Explain briefly.  
 (b) Define  $I_{CBO}$  and  $I_{CEO}$ .

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**Set No. 2**

- (c) What is the order of magnitude of  $I_{CBO}$  for Si transistor and Ge transistor?  
How does  $I_{CBO}$  vary with temperature? [8+4+4]
7. (a) Explain common emitter configuration of a BJT and draw the input and output characteristics.
- (b) Compare different parameters of CB , CE, CC configurations. [10+6]
8. Derive the expression for input resistance with feedback  $R_{if}$  and output resistance,  $R_{of}$  with following feedback configurations based on their equivalent circuits.
- (a) Voltage shunt feedback amplifier
- (b) Current series feedback amplifier. [8+8]

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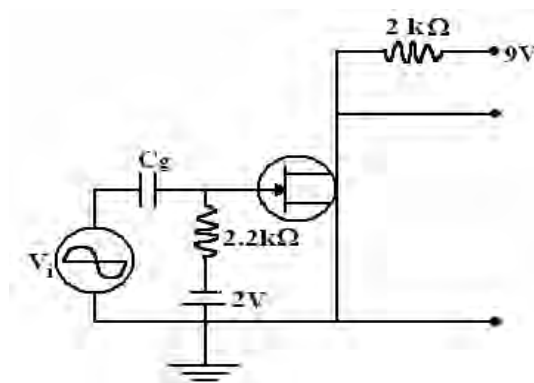


Figure 2:

6. (a) When an electron is placed in a magnetic field with a period of rotation  $T = [35.5/B] 10^{-12}$  sec. Show that the trajectory of electron is a circle.  
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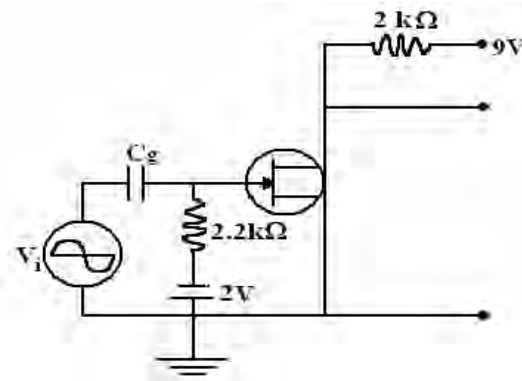


Figure 3:

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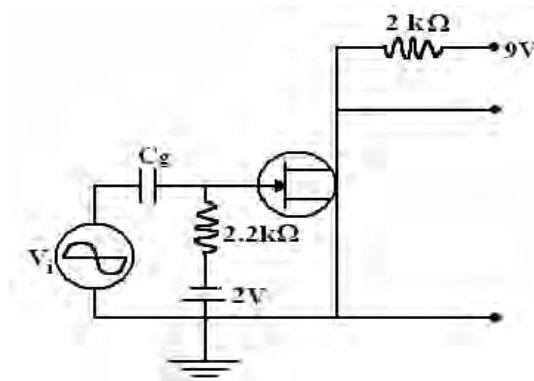


Figure 4:

- When an electron is placed in a magnetic field with a period of rotation  $T = [35.5/B] 10^{-12}$  sec. Show that the trajectory of electron is a circle.
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